

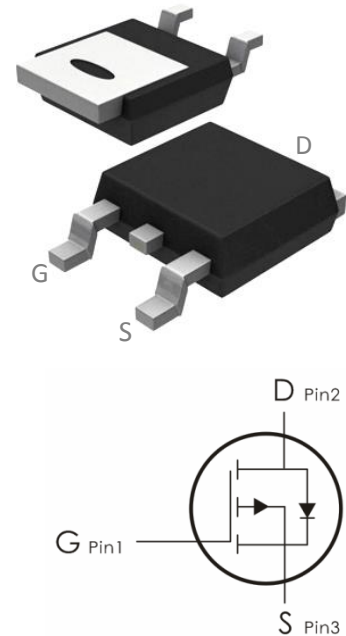
Description:

This P-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=-40V, I_D=-35A, R_{DS(on)} < 16m\Omega @ V_{GS}=-10V$ (Typ: $11m\Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra $R_{DS(on)}$.
- 5) Excellent package for good heat dissipation.



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DD016PG	D016P	TO- 252	2500 pcs/Reel

Absolute Maximum Ratings: ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	-35	A
	Continuous Drain Current- $T_C=100^\circ C$	-24.5	
I_{DM}	Pulsed Drain Current ¹	-140	
P_D	Power Dissipation $T_C=25^\circ C$	60	mJ
	Power Dissipation $T_C=100^\circ C$	30	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +175	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case ¹	2.5	$^\circ C/W$

Electrical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250 μ A	-40	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =-40V	---	---	-1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	Gate-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =-250 μ A	-1	-1.6	-2.5	V
R _{DS(ON)}	Drain-Source On Resistance	V _{GS} =-10V, I _D =-10A	---	11	16	m Ω
		V _{GS} =-4.5V, I _D =- 5A	---	16	22	
G _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-5A	15	---	---	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-20V, V _{GS} =0V, f=1MHz	---	1800	---	pF
C _{oss}	Output Capacitance		---	260	---	
C _{rss}	Reverse Transfer Capacitance		---	150	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =-20V, R _L =1.6 Ω R _{GEN} =3 Ω , V _{GS} =-10V	---	10	---	ns
t _r	Rise Time		---	24	---	ns
t _{d(off)}	Turn-Off Delay Time		---	40	---	ns
t _f	Fall Time		---	9	---	ns
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-20V, I _D =-8A	---	45	---	nC
Q _{gs}	Gate-Source Charge		---	6	---	nC
Q _{gd}	Gate-Drain “Miller” Charge		---	11	---	nC
Drain-Source Diode Characteristics						
V _{SD}	Source-Drain Diode Forward Voltage	V _{GS} =0V, I _S =-10A,	---	---	-1.2	V
I _{SD}	Source-Drain Current(Body Diode)	V _D =V _G =0V	---	---	-29.1	A

Notes:

1.Repetitive Rating: Pulse width limited by maximum junction temperature

Typical Characteristics: ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

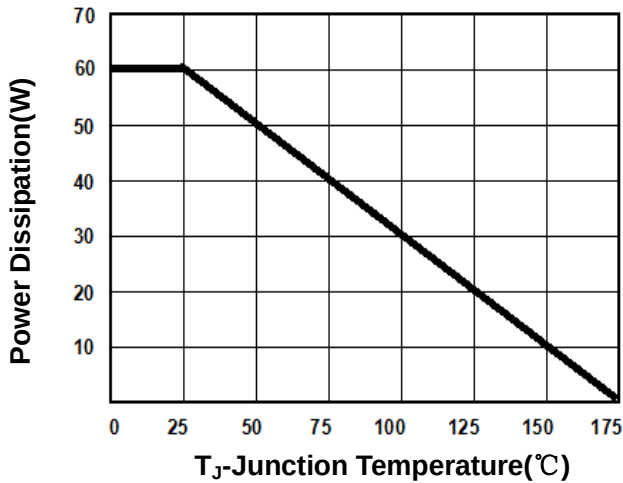


Figure1. Power Dissipation

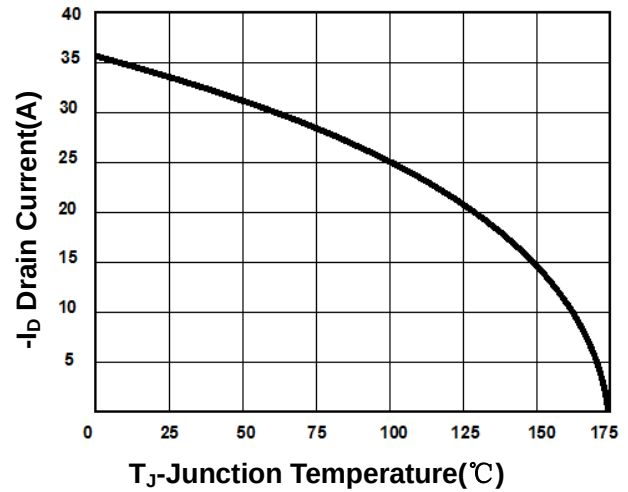


Figure2. Drain Current

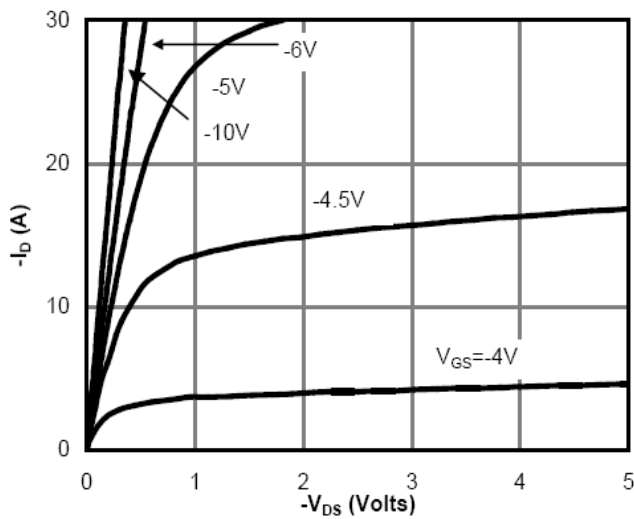


Figure3. Output Characteristics

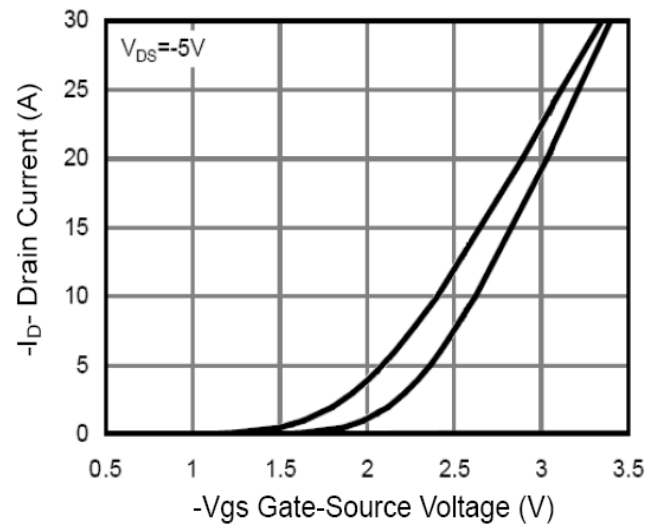
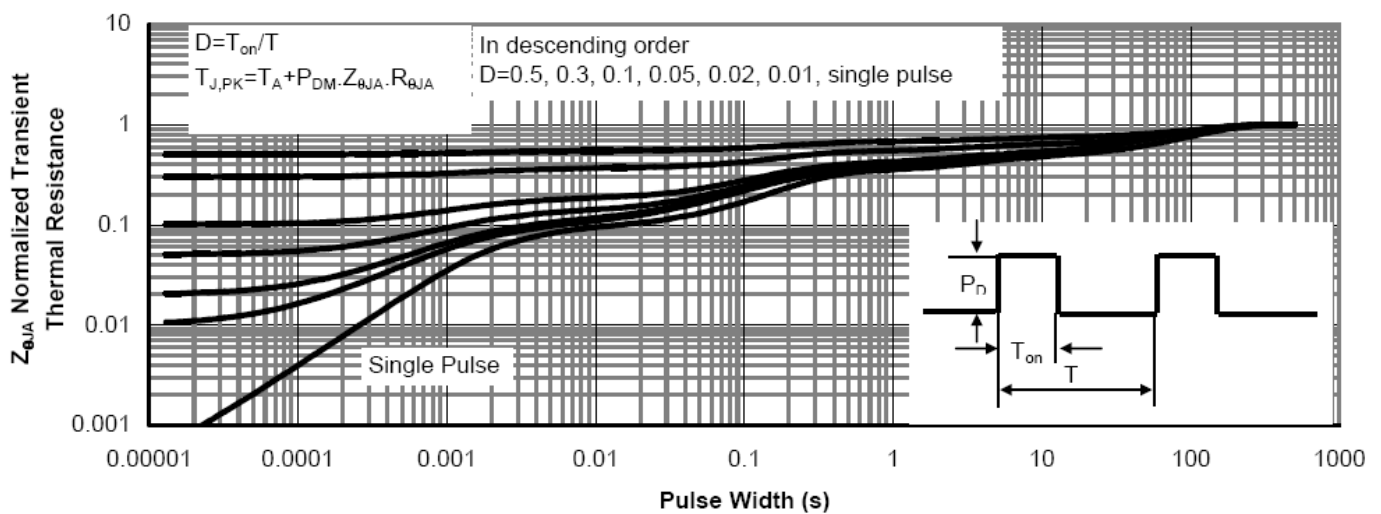
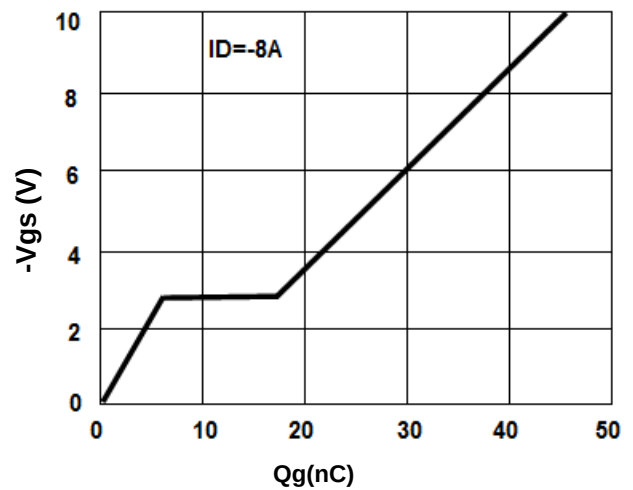
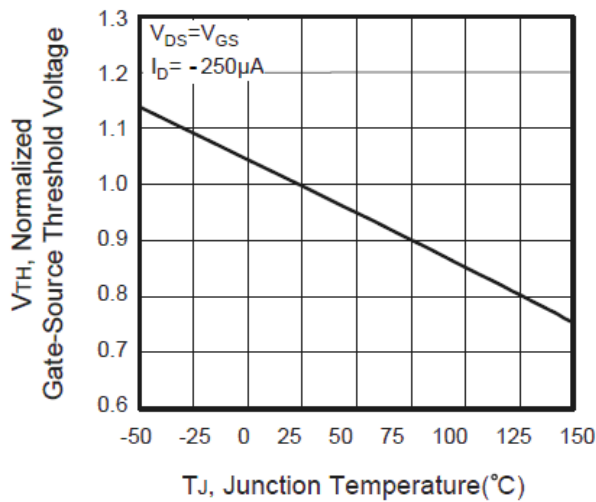
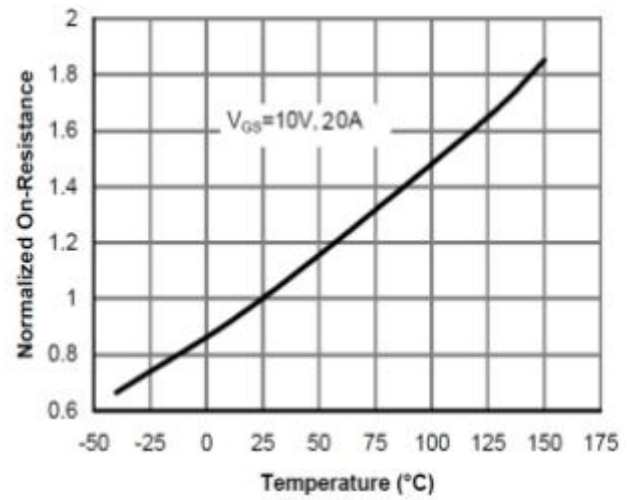
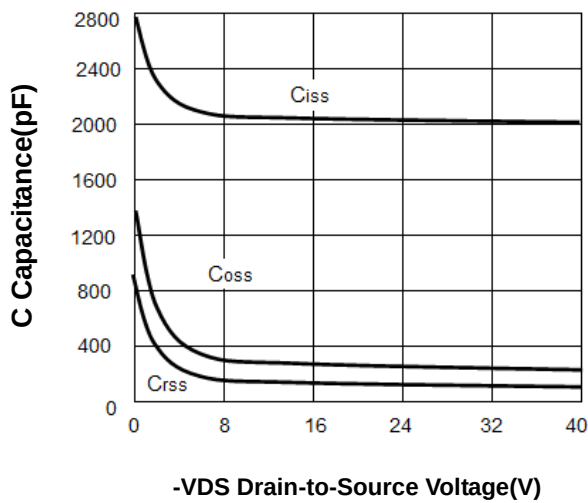


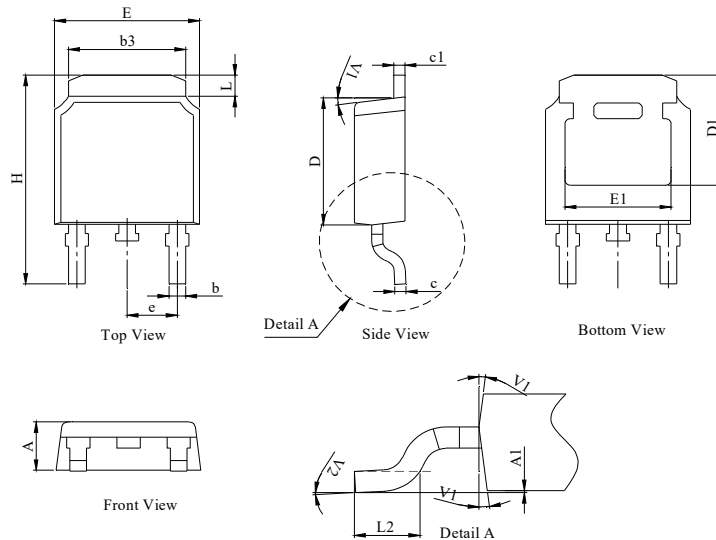
Figure4. Transfer Characteristics



TO-252 Package Information

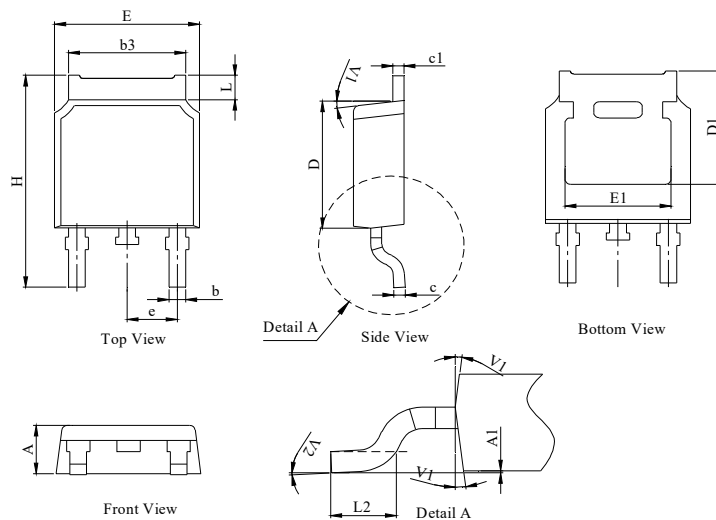
Package Outline Type-A

UNIT: mm



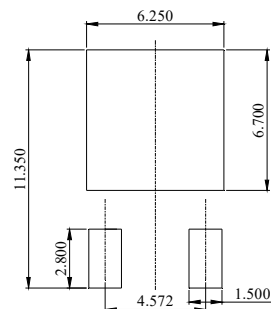
DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	2.18	2.30	2.39
A1	0	--	0.13
b	0.64	0.76	0.89
c	0.40	0.50	0.61
c1	0.46	0.50	0.58
D	5.97	6.10	6.23
D1	5.05	--	--
E	6.35	6.60	6.73
E1	4.32	--	--
b3	5.21	5.38	5.55
e	2.29 BSC		
H	9.40	10.00	10.40
L	0.89	--	1.27
L2	1.40	--	1.78
V1	7° REF		
V2	0°	--	6°

Package Outline Type-B



DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	2.10	2.30	2.40
A1	0	--	0.13
b	0.66	0.76	0.86
b3	5.21	5.38	5.55
c	0.40	0.50	0.60
c1	0.44	0.50	0.58
D	5.90	6.10	6.30
D1	5.30REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.29 BSC		
H	9.50	10.00	10.70
L	1.09	--	1.21
L2	1.35	--	1.65
V1	7° REF		
V2	0°	--	6°

Recommended Soldering Footprint



Marking Information:

①. Doingter LOGO

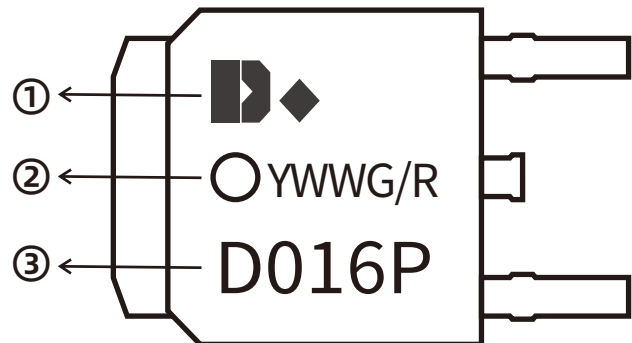
②. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)

③. Part NO.



Previous Version

Version	Date	Subjects (major changes since last revision)
1.1	2026-01-19	Release of final version

Attention :

- Information furnished in this document is believed to be accurate and reliable. However, Shenzhen Doingter Semiconductor Co.,Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it.
- Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Shenzhen Doingter complies with the agreement. Products and information provided in this document have no infringement of patents.
- Shenzhen Doingter assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.



Is

a registered trademark of Shenzhen Doingter Semiconductor Co., Ltd. Copyright © 2013

Shenzhen Doingter Semiconductor Co.,Ltd. Printed All rights reserved.